Serial No. 10/662,391 Docket No. 2207/1211902

Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the aboveidentified application.

Listing of Claims:

- 1. (currently amended) A semiconductor package having a trace designed as a dual referenced microstrip structure, comprising:
- a <u>dual referenced microstrip</u> transmission line <u>having a predefined characteristic</u> impedance and characteristic impedance value;
 - a first conductive plane;
- a first dielectric layer provided between the <u>dual referenced microstrip</u>-transmission line and the first conductive plane;
 - a second conductive plane; and
- a second dielectric layer provided between the first conductive plane and the second conductive plane, wherein an inter-plane impedance is an impedance of the first conductive plane with reference to the second conductive plane; and
- wherein at least one physical parameter associated with the inter-plane impedance is selected such that the characteristic impedance value of the dual referenced transmission line does not exceed the characteristic impedance tolerance value with respect to the first and second conductive planes.
- 2. (currently amended) The dual referenced microstrip structure semiconductor package of claim 1, wherein an absolute value of a difference between a characteristic impedance of the dual referenced microstrip transmission line referenced to the first conductive plane and the a characteristic impedance of the dual referenced microstrip transmission line referenced to the second conductive plane is less than a the predetermined characteristic impedance tolerance value.
- 3. (currently amended) The <u>semiconductor package dual referenced microstrip structure of</u> claim 1, wherein the characteristic impedance of <u>a-the dual referenced</u> transmission line in the

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dual referenced microstrip structure referenced to a first reference plane minus the characteristic impedance referenced to a second reference plane is less than a predetermined value is calculated as a function of at least one physical parameter associated with the inter-plane impedance.

selected such that the characteristic impedance value of the dual referenced transmission line does not exceed the characteristic impedance tolerance value with respect to the first and second reference planes.

- 5. (currently amended) The dual referenced transmission line of claim 4, wherein an absolute value of a difference between the a characteristic impedance of the signal routing tracetransmission line referenced to the first reference plane and a characteristic impedance of versus the signal routing trace transmission line referenced to the second reference plane is less than the predetermined characteristic impedance tolerance valueless than a predetermined percentage of the characteristic impedance of the transmission line.
- 6. (currently amended) The dual referenced transmission line of claim 4, wherein the difference between the characteristic impedance of the signal routing trace transmission line is calculated as a function of at least one physical parameter associated with the inter-plane impedance referenced to the first reference plane versus the transmission line referenced to the second reference plane is less than a predetermined value.

- 7. (currently amended) The <u>dual referenced transmission linesemiconductor package</u> of claim 62, wherein the predetermined <u>characteristic impedance tolerance</u> value is less than two Ohms.
- 8. (new) The semiconductor package of claim 1, wherein the microstrip dual referenced transmission line characteristic impedance tolerance value is proportional to the inter-plane impedance.
- 9. (new) The semiconductor package of claim 1, wherein the <u>dual referenced microstrip</u> transmission line characteristic impedance tolerance value is directly proportional to the interplane impedance.
- 10. (new) The semiconductor package of claim 1, wherein the physical parameter associated with the inter-plane impedance is at least one of: thickness of the second dielectric layer; the relative dielectric constant of the second dielectric layer; the surface area of the first and second conductive planes; the thickness of the conductive material of the first or second conductive planes; the type of conductive material of the first or second conductive planes; placement of discrete capacitors shunting the first and second conductive planes; and the number of connections which the semiconductor package makes to a die and a printed circuit board.
- 11. (new) The dual referenced transmission line of claim 5, wherein the predetermined characteristic impedance tolerance value is two Ohms.
- 12. (new) The dual referenced transmission line of claim 4, wherein the characteristic impedance tolerance value is proportional to the inter-plane impedance.
- 13. (new) The dual referenced transmission line of claim 4, wherein the characteristic impedance tolerance value is directly proportional to the inter-plane impedance.

14. (new) The dual referenced transmission line of claim 4, wherein the physical parameter associated with the inter-plane impedance is at least one of: thickness of a dielectric layer between the first and second reference planes; the relative dielectric constant of a dielectric layer between the first and second reference planes; the surface area of the first and second reference planes; the thickness of the conductive material of the first or second reference planes; the type of conductive material of the first or second reference planes; placement of discrete capacitors shunting the first and second reference planes; and the number of connections which a package including semiconductor circuits makes to a die and a printed circuit board having the dual referenced transmission line.